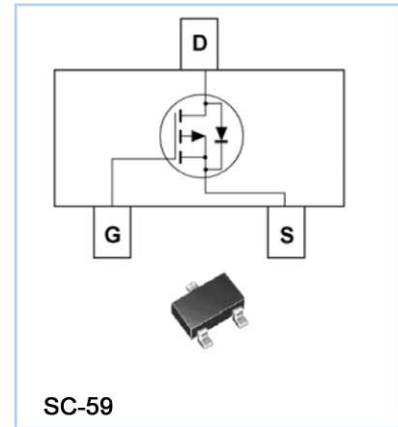# P-Channel Enhancement Mode MOSFET

Feature

- -16V/-4A, $R_{DS(ON)} = 90m\Omega\,(MAX)$ @$V_{GS} = -4.5V$.

  $R_{DS(ON)} = 130m\Omega\,(MAX)$ @$V_{GS} = -2.5V$.

- Super High dense cell design for extremely low $R_{DS(ON)}$

- Reliable and Rugged

- SC-59 for Surface Mount Package

SC-59

Applications

- Power Management

  Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings $T_A=25°C$ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-16	V
Gate-Source Voltage	V_{GS}	± 8	V
Drain Current-Continuous	I_D	-4	A

## Electrical Characteristics $T_A=25°C$ Unless Otherwise noted

| Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	VGS=0V, ID=-250μA	-16	-	-	V
Zero-Gate Voltage Drain Current	IDSS	VDS=-12V, VGS=0V	-	-	-1	μA
Gate Body Leakage Current, Forward	IGSSF	VGS=8V, VDS=0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	VGS=-8V, VDS=0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	VGS(th)	VGS= VDS, ID=-250μA	-0.5	-	-1.5	V
Static Drain-source On-Resistance	RDS(ON)	VGS =-4.5V, ID =-4.0A	-	-	90	mΩ
		VGS =-2.5V, ID =-2.0A	-	-	130	mΩ
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	VGS =0V, IS=-1.25A			-1.2	V

Typical Characteristics
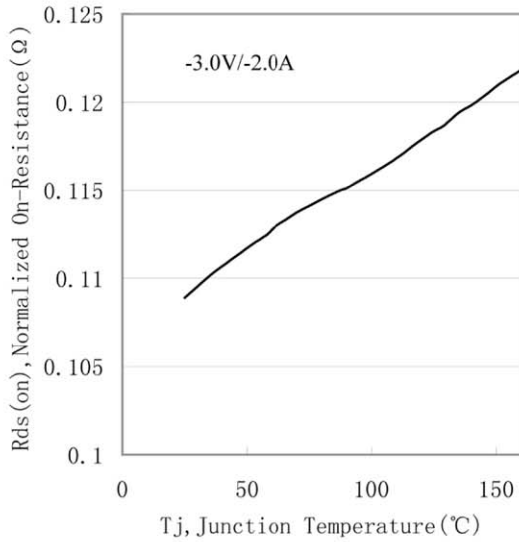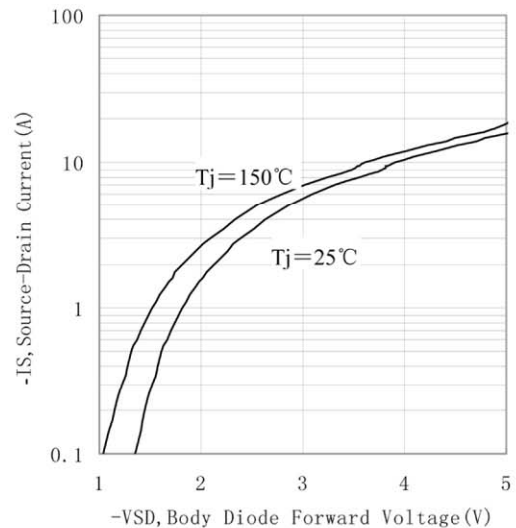

Figure 5．On-Resistance Variation with Temperature
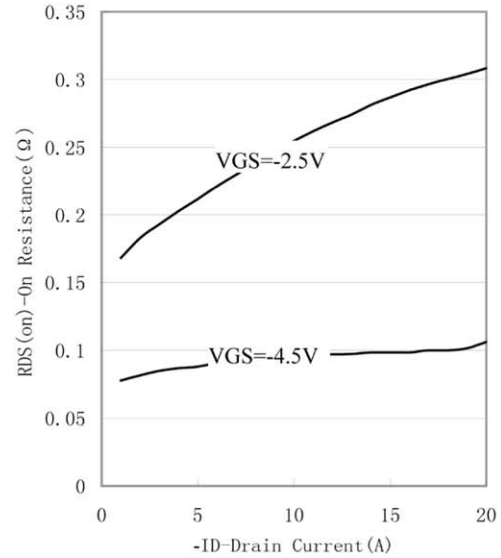
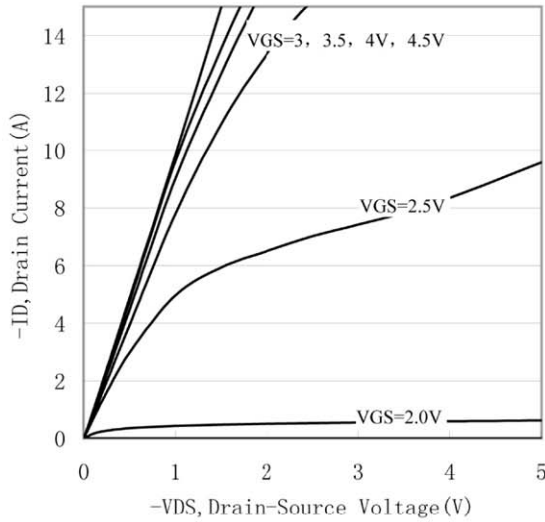**Figure 6．On-Resistance vs. Drain Current**
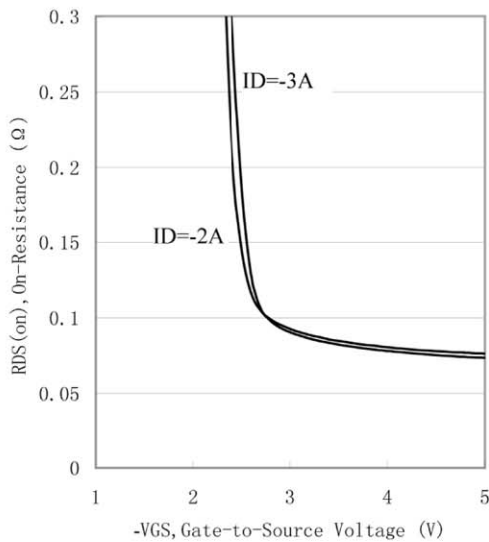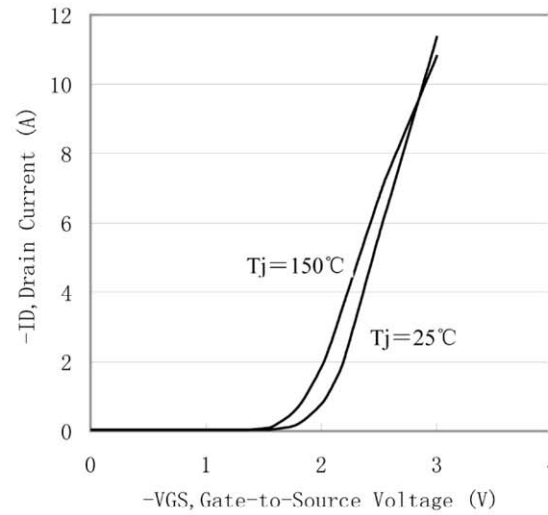

Figure 7．On-Resistance vs. Gate-to-Source Voltage

Figure 8．Source-Drain Diode Forward Voltage
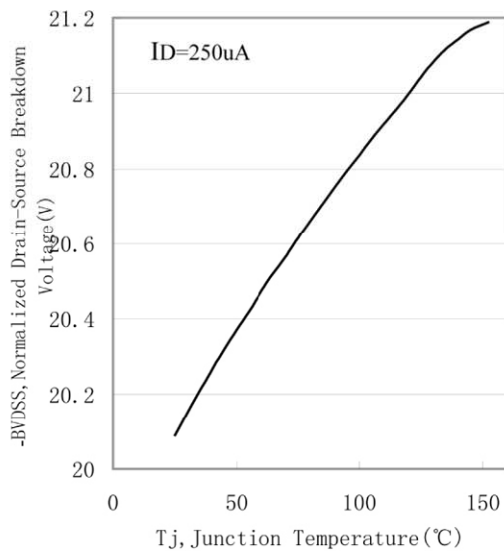
REV.07

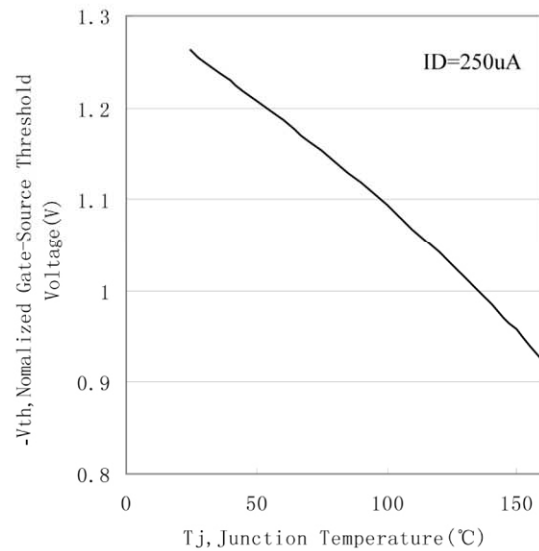www.shike.tw

Typical Characteristics

Figure 1. Output Characteristics

Figure 2. Transfer Characteristics

Figure 3. Breakdown Voltage Variation with Temperature

Figure 4. Gate Threshold Variation with Temperature